

Ph.D. Thesis “VLSI-Compatible Si/SiGe/Si p-MOSFETs” University of Toronto, 1994.

Patents

1. S.P. Voinigescu, A. Tomkins, A. Balteanu, I. Sarkas and K. Laskin “Radio Antenna Switch” US Patent No: 8,676,136
2. S.P. Voinigescu, A. Timonov, S.T. Nicolson, A. Nachman, E. Laskin, G.V. Eleftheriades “High Frequency System on Chip Transceiver” US Patent No: 8,139,625
3. M.A. Copeland, S.P. Voinigescu, D. Marchesan, “Method and apparatus for performing image signal rejection” US Patent No: 6542724.
4. S.P. Voinigescu and M.C. Maliepaard on "High frequency noise and impedance matched integrated circuits" US Patent No: 5789799
5. X-M. Li, S.P. Voinigescu, "Method for forming a lateral bipolar transistor", US Patent No: 5624856.

Books

S.P. Voinigescu, High Frequency Integrated Circuits, Cambridge University Press, 2013

Book Chapters

1. S.P. Voinigescu, S.T. Nicolson, E. Laskin, K. Tang, and P. Chevalier, “SiGe BiCMOS and CMOS Transceiver Blocks for Automotive Radar and Imaging Applications in the 80-160 GHz Range”, in “Analog Circuit Design” pp. 303-326, edited by Herman Casier, Michiel Steyaert and Arthur H.M. van Roermund, 2008, Springer 2008, ISBN 978-1-4020-8262-7.
2. S.T. Nicolson, K.W. Tang, T.O. Dickson, P. Chevalier, B. Sautreuil, and S. P. Voinigescu, Design of Silicon Integrated Circuit W-Band Low Noise Amplifiers,” in “*Wireless technologies: Circuits, Systems, and Devices*,” edited by Krzysztof Iniewski, CRC Press, Oct. 2007, ISBN:978-0-84937-9-963.
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Journal Papers

1. A. Balteanu, S. Shopov, and S.P. Voinigescu, "A High Modulation-Bandwidth, 110-GHz Power-DAC Cell for IQTransmitter Arrays with Direct Amplitude and Phase Modulation," *IEEE JSSC*, Vol.49, No.10, pp.xxx, October 2014.
2. S. Shopov, A. Balteanu, and S.P. Voinigescu, "A 19-dBm, 15-GBaud, 9-bit SOI CMOS Power-DAC Cell for High Order QAM W-Band Transmitters " *IEEE JSSC*, Vol.49, No.7, pp.653-1664, July 2014.
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3. Y. Fu and S.P.Voinigescu, "A 108-GHz Retimer based on 1.8V Quasi-ECL MOS-HBT SiGe BiCMOS Logic," *IEEE CSICS*, Monterey, CA, October 2013.
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